CMD65R290/CMU65R290

650V, 0.27Ω typ., 13A N-Channel Super Junction Power MOSFET

General Description

The 65R290 is power MOSFET using Cmos's advanced super junction technology that can realize very low on resistance and gate charge. It will provide much high efficiency by using optimized charge coupling technology. These user friendly devices give an advantage of low EMI to designers as well as low switching loss.

Product Summary

BV_{DSS}	$R_{DS(on)}$ max.	I_D
650V	0.3Ω	13A

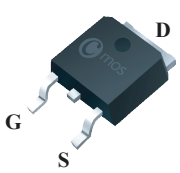
Applications

- Charger
- Adaptor
- Power Supply

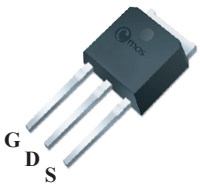
Features

- Multi-layer Epitaxial Chip Technology
- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

TO-252/TO-251 Pin Configuration



TO-252
CMD65R290



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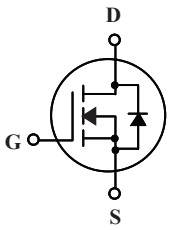

Absolute Maximum Ratings

Symbol	Parameter		Rating	Units
V_{DS}	Drain-Source Voltage		650	V
V_{GS}	Gate-Source Voltage		±30	V
I_D@T_C=25℃	Continuous Drain Current	(Note 1)	13	A
I_D@T_C=100℃	Continuous Drain Current		8	A
I_{DM}	Pulsed Drain Current	(Note 2)	52	A
EAS	Single Pulse Avalanche Energy	(Note 3)	453	mJ
P_D@T_C=25℃	Total Power Dissipation		132	W
T_{STG}	Storage Temperature Range		-55 to 150	℃
T_J	Operating Junction Temperature Range		-55 to 150	℃

Thermal Data

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	127	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-case	0.95	℃/W

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Electrical Characteristics (T_J=25℃ , unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	650	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=6A	---	0.27	0.3	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=650V , V_{GS}=0V, T_j =25℃	---	---	1	uA
		V_{DS}=650V , V_{GS}=0V , T_j =150℃	---	5	---	
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V, I_D =6A	---	7	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	9	---	Ω
Q_g	Total Gate Charge	I_D=7.5A V_{DS}=480V V_{GS}=10V	---	24	---	nC
Q_{gs}	Gate-Source Charge		---	5	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DS}=400V V_{GS}=10V I_D=7.5A R_G=25Ω	---	14	---	ns
T_r	Rise Time		---	24	---	
$T_{d(off)}$	Turn-Off Delay Time		---	97	---	
T_f	Fall Time		---	22	---	
C_{iss}	Input Capacitance	V_{DS}=100V , V_{GS}=0V , f=1MHz	---	660	---	pF
C_{oss}	Output Capacitance		---	40	---	
C_{rss}	Reverse Transfer Capacitance		---	2.3	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	13	A
I_{SM}	Pulsed Source Current		---	---	52	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=12A ,T_J=25℃	---	0.88	1.2	V
t_{rr}	Reverse Recovery Time	di/dt = 100A/μs V_{DS}=100V , I_{SD}=7.5A	---	250	---	ns
Q_{rr}	Reverse Recovery Charge		---	2.94	---	μC

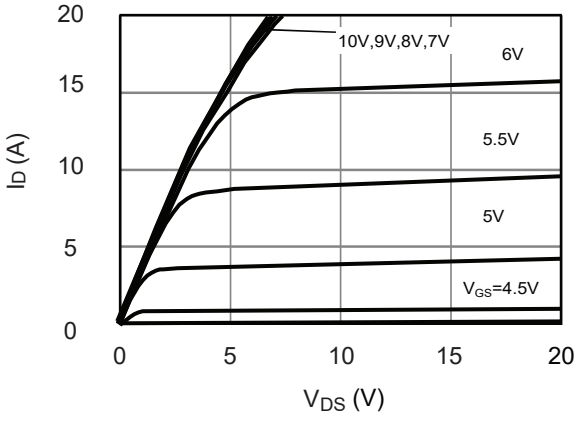
Notes:

1.Limited by Tj,max. Maximum Duty Cycle D = 0.50

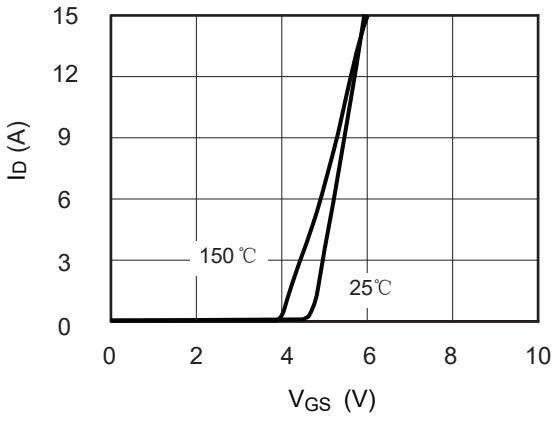
2.Pulse width tp limited by Tj,max.

3.The EAS data shows Max. rating .The test condition is V_{DS}=80V , V_{GS}=10V , L=30mH , I_{AS}=5.5A.

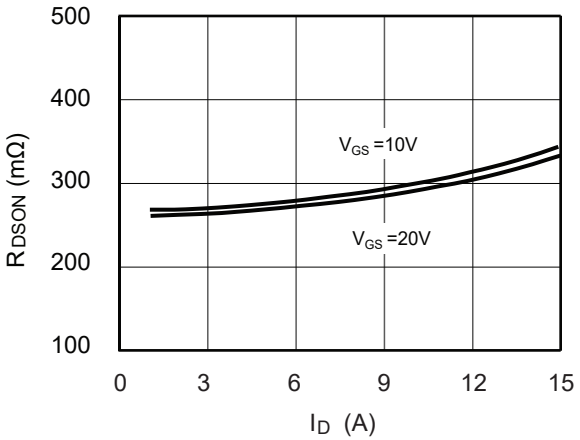
Typical Characteristics



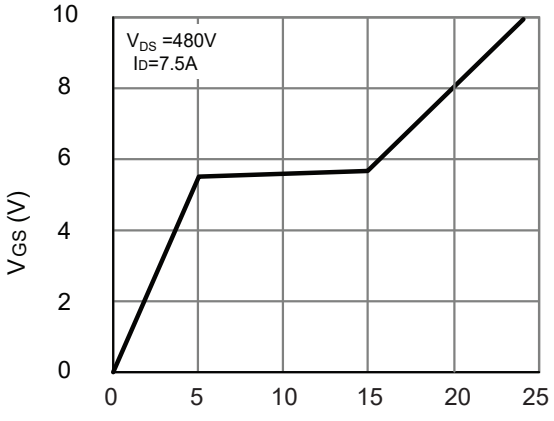
Output Characteristics



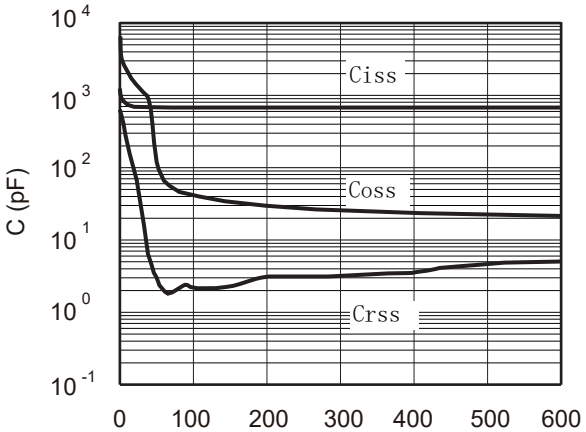
transfer characteristics



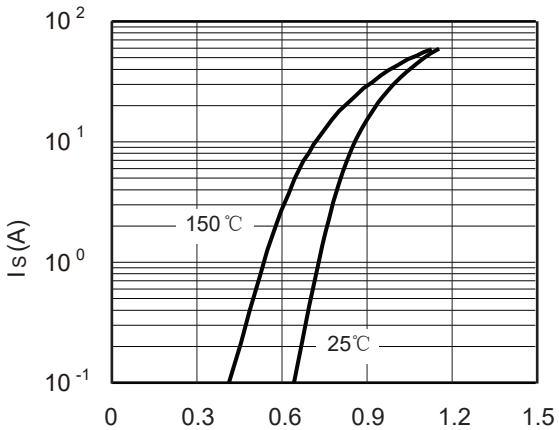
drain-source on-resistance



Gate charge vs gate-source voltage



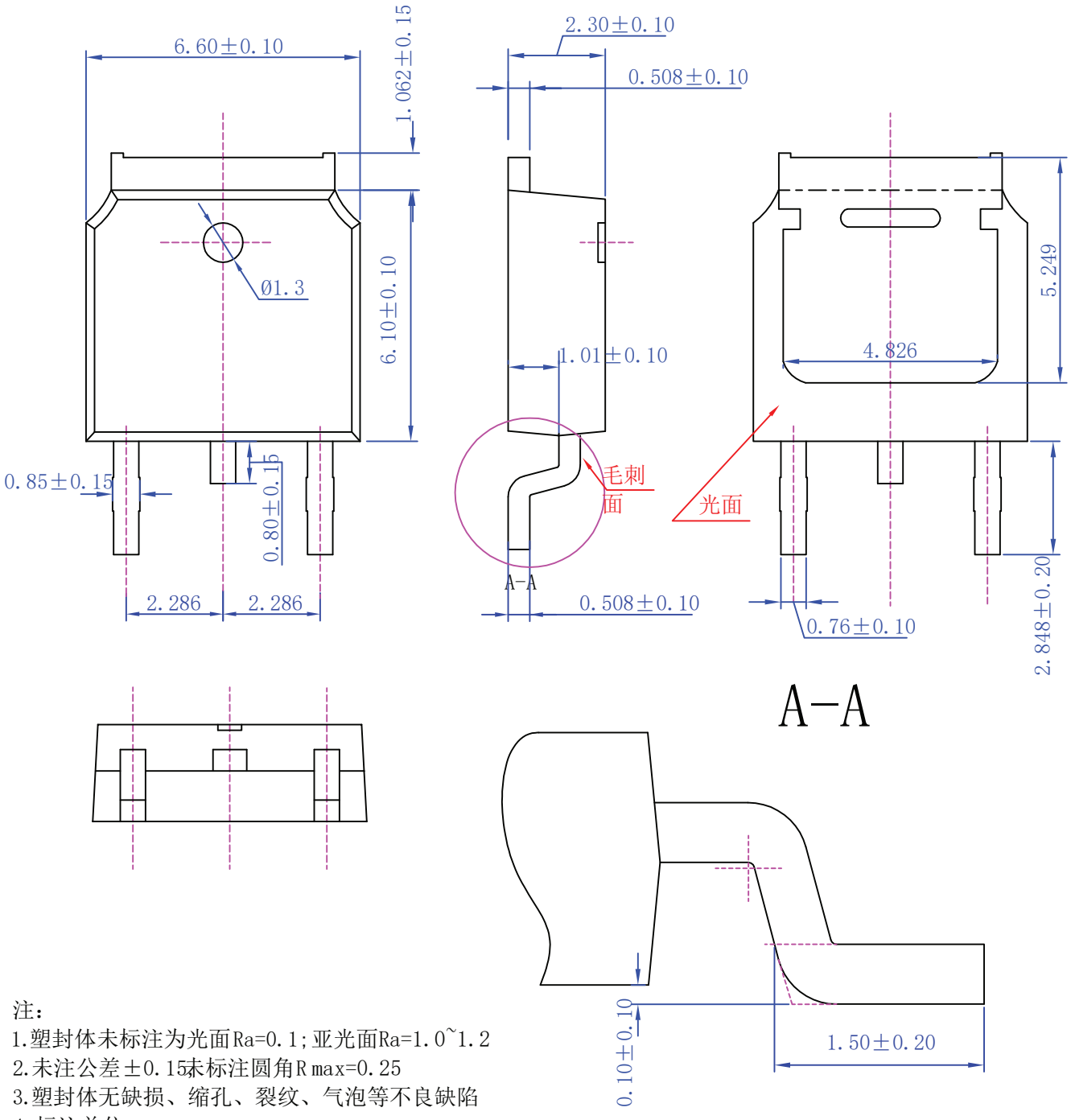
Capacitance Characteristics



Body-Diode Characteristics

Package Dimension

TO-252 Unit :mm



注：
1.塑封体未标注为光面Ra=0.1;亚光面Ra=1.0~1.2
2.未注公差±0.15未标注圆角R max=0.25
3.塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
4.标注单位mm
5.顶针孔不允许凸出塑封体表面

Package Dimension

TO-251A Unit :mm